



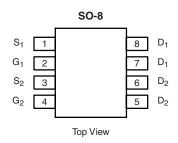
Dual N-Channel 60-V (D-S), 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
60	0.080 at $V_{GS} = 10 \text{ V}$	± 3.7		
	0.100 at V _{GS} = 4.5 V	± 3.4		

FEATURES

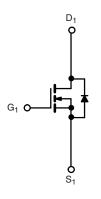
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC



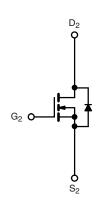


Ordering Information: Si9945AEY-T1-E3 (Lead (Pb)-free)

Si9945AEY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	60	v	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current /T 175 °C\8	T _A = 25 °C	I_	± 3.7		
Continuous Drain Current (T _J = 175 °C) ^a	T _A = 70 °C	- I _D	± 3.2	^	
Pulsed Drain Current		I _{DM}	25	Α	
Continuous Source Current (Diode Conduction) ^a		I _S	2		
Mariana Barra Birainatian	T _A = 25 °C	P _D	2.4	_ w	
Maximum Power Dissipation ^a	T _A = 70 °C	' b	1.7		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
hungstien to Anahienta	t ≤ 10 s	R _{thJA}		62.5	°C/W	
Junction-to-Ambient ^a	Steady State	' ¹thJA	93			

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

Si9945AEY

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SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions Min. Typ.		Max.	Unit			
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		3	V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			1	μΑ		
					10			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α		
Davis Course On Otata Basistana	B ·	V _{GS} = 10 V, I _D = 3.7 A		0.06	0.080	0		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 3.4 \text{ A}$		0.075	0.100	Ω		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 3.7 A		11		S		
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.0 \text{ A}, V_{GS} = 0 \text{ V}$			1.2	V		
Dynamic ^b								
Total Gate Charge	Q_g			11	20			
Gate-Source Charge	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3.7 \text{ A}$		2		nC		
Gate-Drain Charge	Q_{gd}			2		1		
Turn-On Delay Time	t _{d(on)}			9	20			
Rise Time	t _r	V_{DD} = 30 V, R_L = 30 Ω		10	20			
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		21	40	ns		
Fall Time	t _f			8	20			
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 2.0 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$		45	80			

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

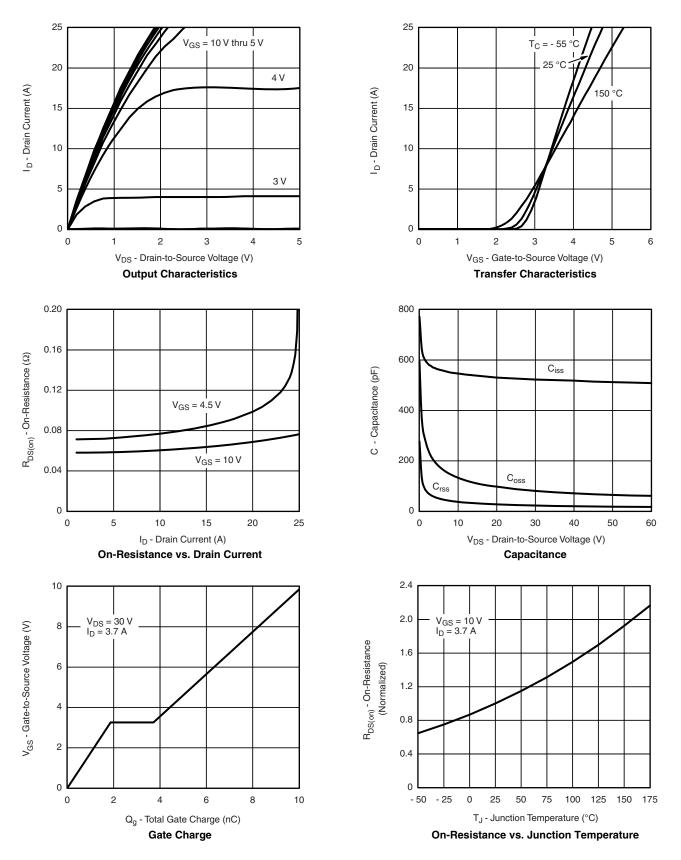
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.





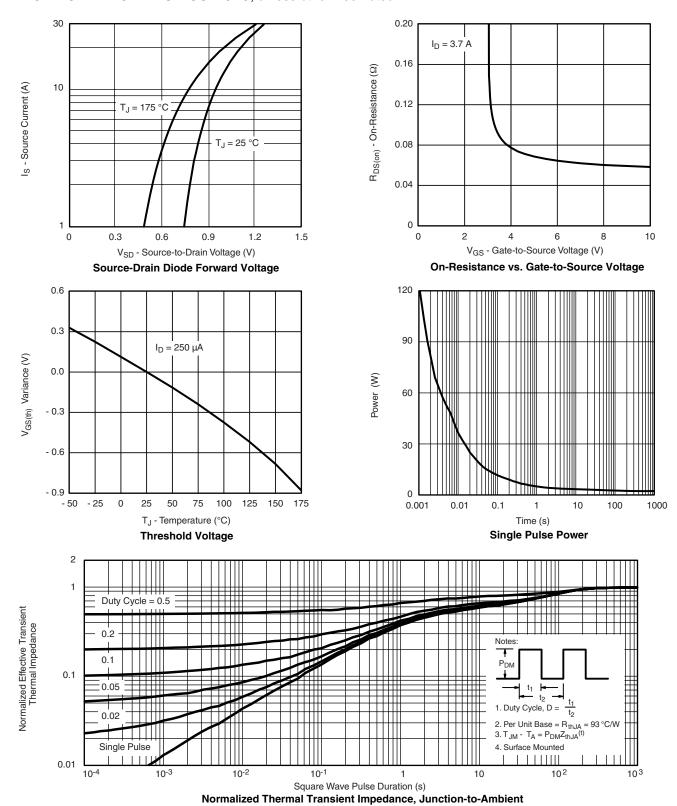
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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